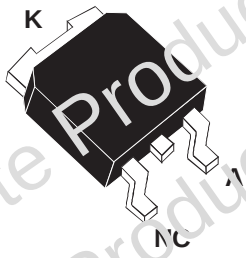
STTA312B

TURBOSWITCH™ ULTRA-FAST HIGH VOLTAGE DIODE

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	3 A
V_{RRM}	1200 V
t_{rr} (typ)	65 ns
V_F (max)	1.7 V



DPAK

FEATURES AND BENEFITS

- SPECIFIC TO THE FOLLOWING OPERATIONS : SNUBBING OR CLAMPING, DEMAGNETIZATION AND RECTIFICATION
- ULTRA-FAST, SOFT RECOVERY
- VERY LOW OVERALL POWER LOSSES AND PARTICULARY LOW FORWARD VOLTAGE
- HIGH FREQUENCY OPERATION
- HIGH REVERSE VOLTAGE CAPABILITY

DESCRIPTION

TURBOSWITCH 1200V drastically cuts losses in all high voltage operations which require extremely fast, soft and noise-free power diodes.

Due to their optimized switching performances they also highly decrease power losses in any associated switching IGBT or MOSFET in all "freewheel mode" operations.

They are particularly suitable in motor control circuitries, or in primary of SMPS as snubber, clamping or demagnetizing diodes. They are also suitable for the secondary of SMPS as high voltage rectifier diodes.

Obsolete Product(s) - Obsolete Product(s)

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1200	V
V_{RSM}	Non repetitive peak reverse voltage		1200	V
$I_{F(RMS)}$	RMS forward current		6	A
I_{FRM}	Repetitive peak forward current	tp = 5 µs F = 5kHz square	35	A
I_{FSM}	Surge non repetitive forward current	tp = 10ms sinusoidal	25	A
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum operating junction temperature		125	°C

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THERMAL AND POWER DATA

Symbol	Parameter	Tests conditions	Value	Unit
$R_{th\ (j-c)}$	Junction to case thermal resistance		6.5	°C/W
P_1	Conduction power dissipation	$I_{F(AV)}$ = 3A, δ = 0.5 Tc = 80°C	6.7	W
P_{max}	Total power dissipation $P_{max} = P_1 + P_3$ (P_3 = 10% P_1)	Tc = 76°C	7.5	W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
V_F **	Forward voltage drop	I_F = 3 A	Tj = 25°C			1.8	V
		I_F = 3 A	Tj = 125°C		1.15	1.7	
I_R *	Reverse leakage current	V_R = 0.8 X V_{RRM}	Tj = 25°C			20	µA
			Tj = 125°C		150	400	µA
Vto	Threshold voltage	Ip < 3.I_{AV}	Tj = 125°C			1.15	V
rd	Dynamic resistance					185	mΩ

Test pulses : * tp = 380 µs, δ < 2%
** tp = 5 ms , δ < 2%

To evaluate the maximum conduction losses use the following equation :
$P = V_{to} \times I_{F(AV)} + rd \times I_F{}^2{}_{(RMS)}$

DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-OFF SWITCHING

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t_{rr}		Tj = 25°C	I_F= 0.5A I_R=1A I_{rr}= 0.25A I_F= 1A dI_F/dt= 50A/µs V_R= 30V		65	115	ns
I_{RM}	Maximum recovery current	Tj = 125°C	I_F= 3A V_R= 600V dI_F/dt = -16A/µs dI_F/dt = -50A/µs		6.0	3.6	A
S factor	Softness factor	Tj = 125°C	V_R= 600V I_F= 3A dI_F/dt = -50A/µs		1.2		-

TURN-ON SWITCHING

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{fr}	Forward recovery time	Tj = 25°C I_F=3A dI_F/dt = 16A/µs Measured at 1.1 x V_{Fmax}			900	ns
V_{FP}	Peak forward voltage				35	V

Obsolete Product(s) - Obsolete Product(s)

Fig. 1: Conduction losses versus average current.

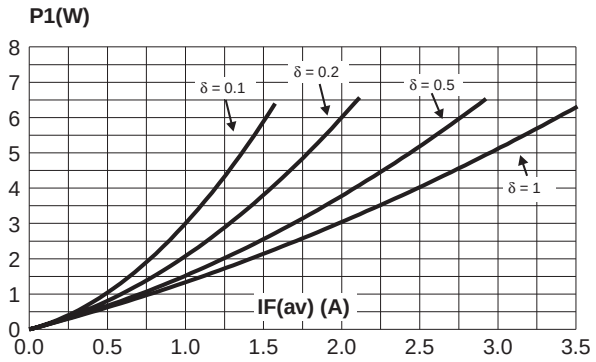


Fig. 2: Forward voltage drop versus forward current (maximum values).

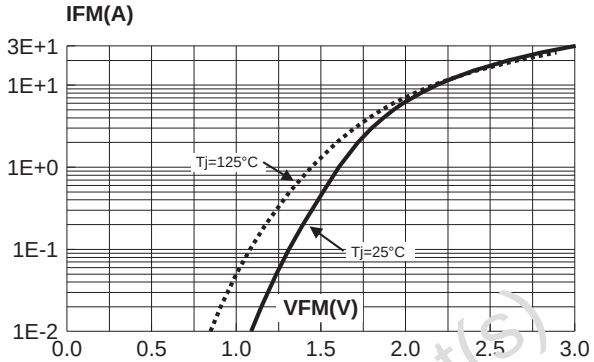


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

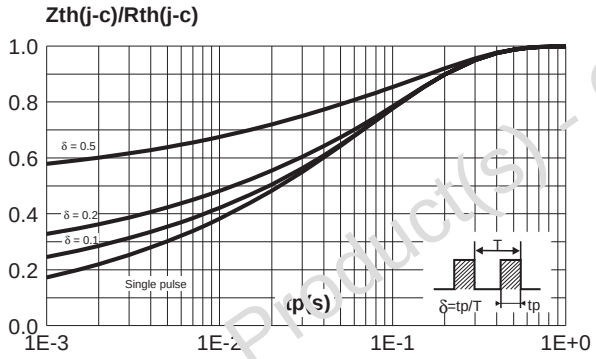


Fig. 4: Peak reverse recovery current versus dI_F/dt (90% confidence).

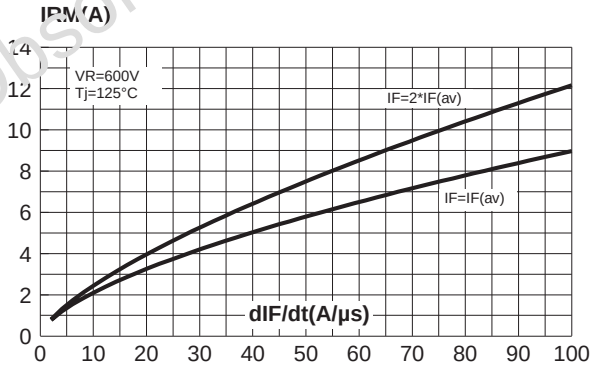


Fig. 5: Reverse recovery time versus dI_F/dt (90% confidence).

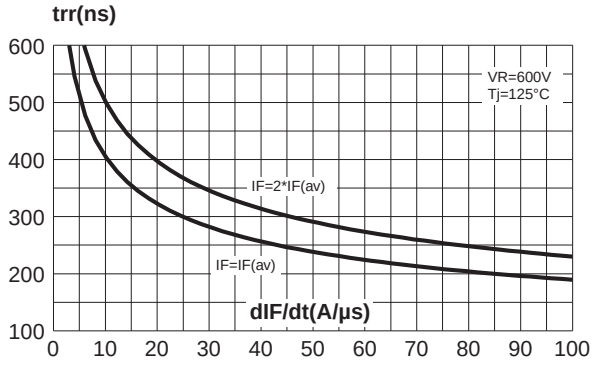
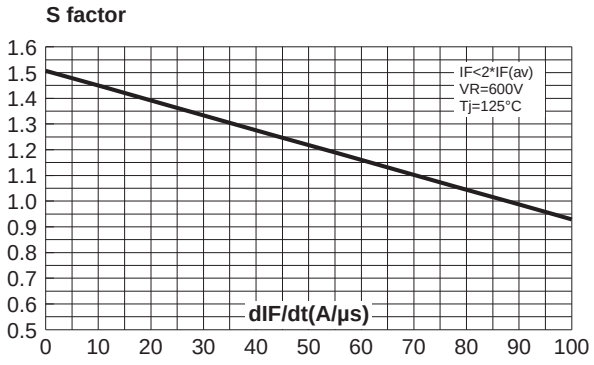


Fig. 6: Softness factor tb/ta versus dI_F/dt (typical values).



Obsolete Product(s) - Obsolete Product(s)

Fig. 7: Relative variation of dynamic parameters versus junction temperature (reference: Tj=125°C).

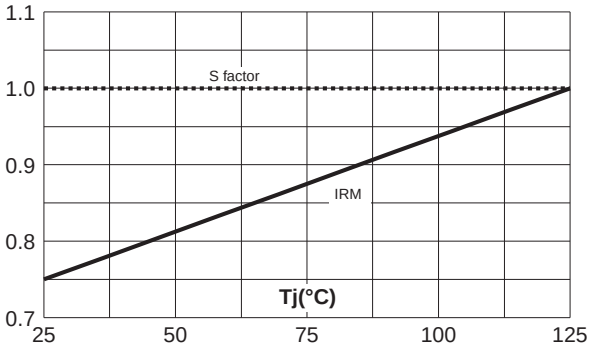


Fig. 8: Transient peak forward voltage versus dI_F/dt (90% confidence).

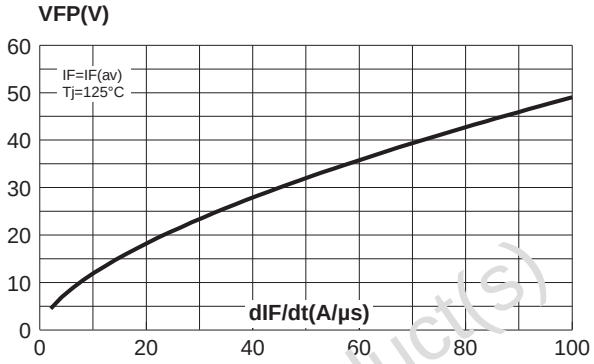
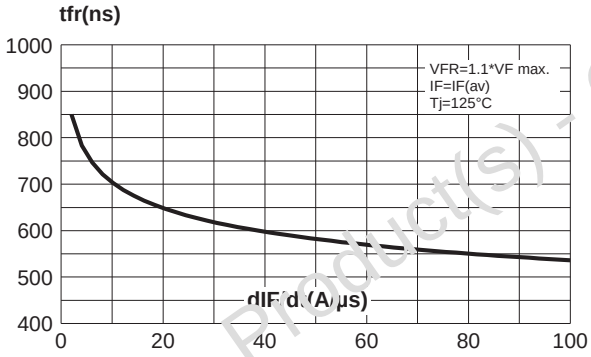


Fig. 9: Forward recovery time versus dI_F/dt (90% confidence).

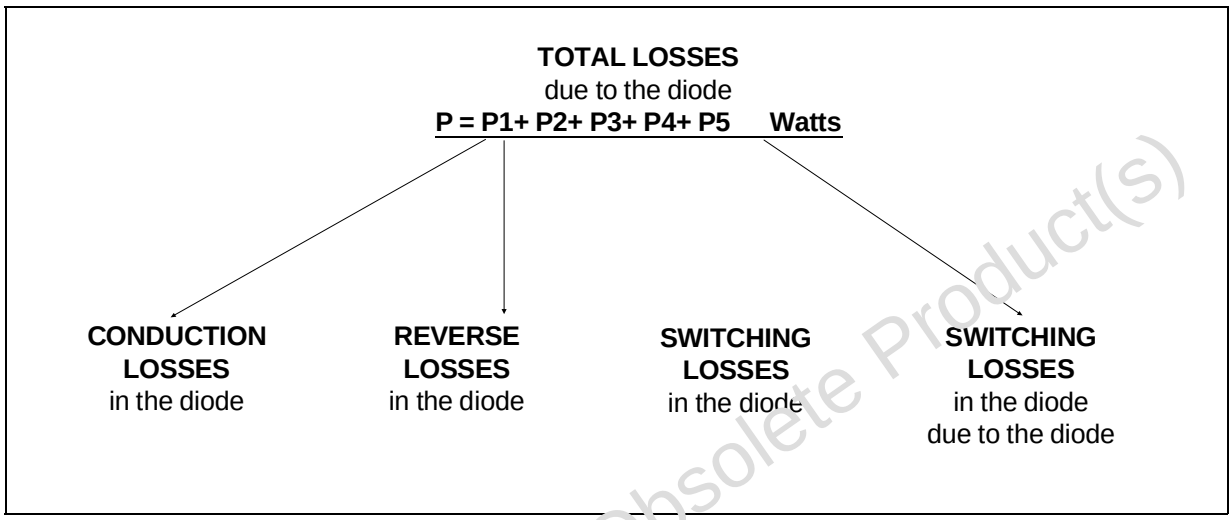


Obsolete Product(s) - Obsolete Product(s)

APPLICATION DATA

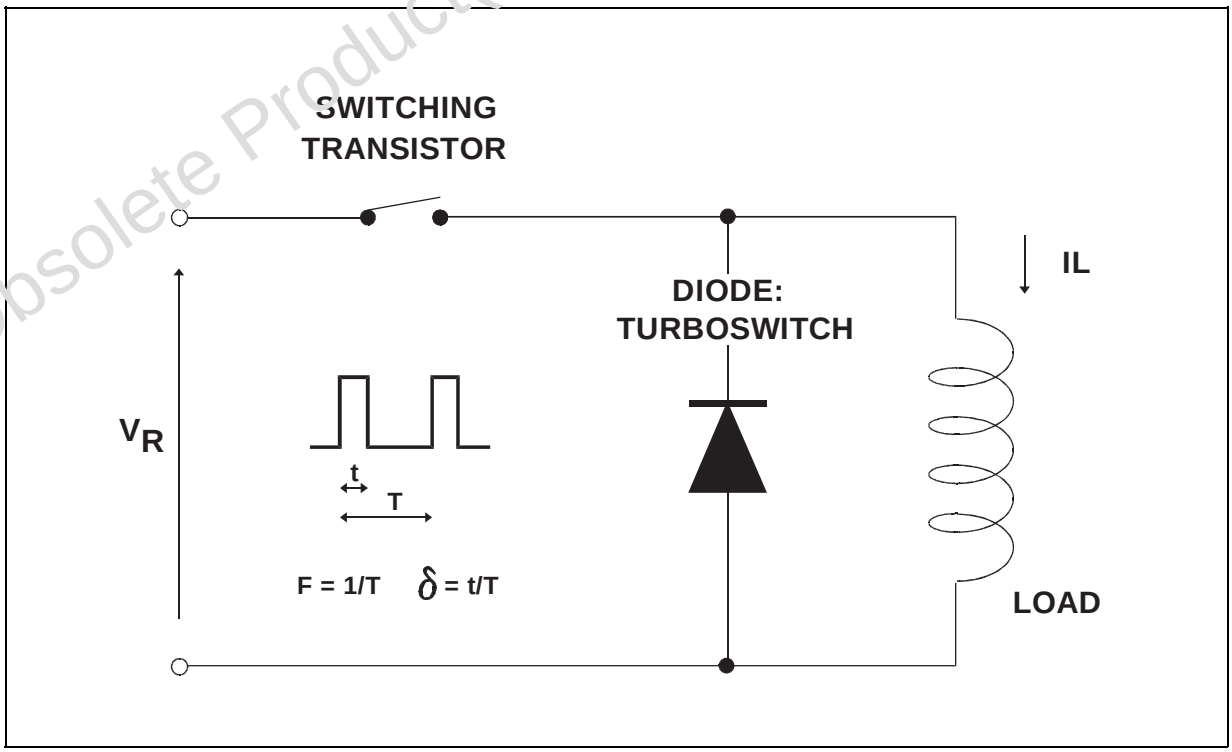
The 1200V TURBOSWITCH^{TM} series has been designed to provide the lowest overall power losses in all frequency or high pulsed current operations.

In such application (fig. A to D), the way of calculating the power losses is given below :



Obsolete Product(s) - Obsolete Product(s)

Fig. A : "FREEWHEEL MODE"**.**



APPLICATION DATA (Cont'd)

Fig. B : SNUBBER DIODE.

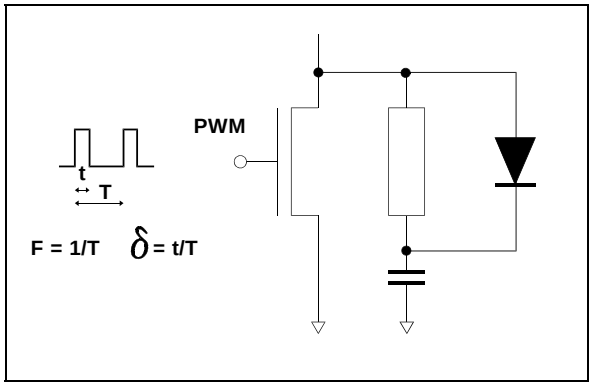


Fig. C : DEMAGNETIZING DIODE.

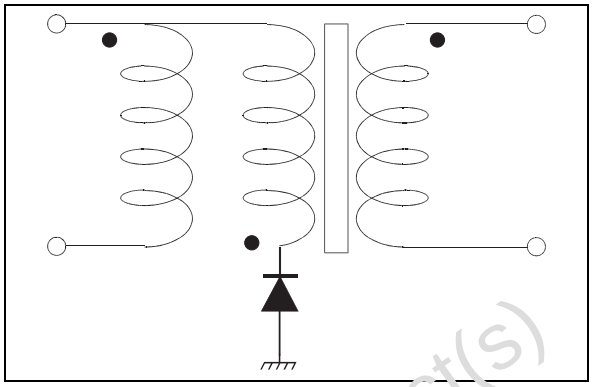


Fig. D : RECTIFIER DIODE.

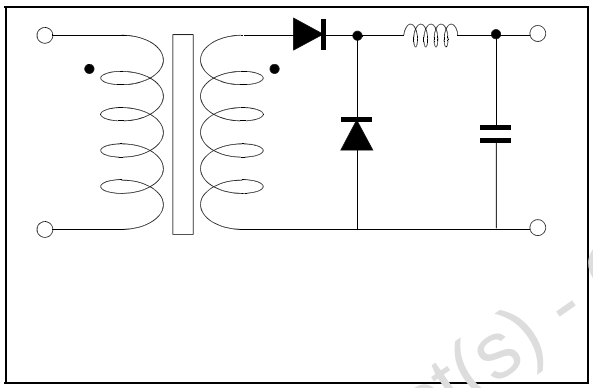
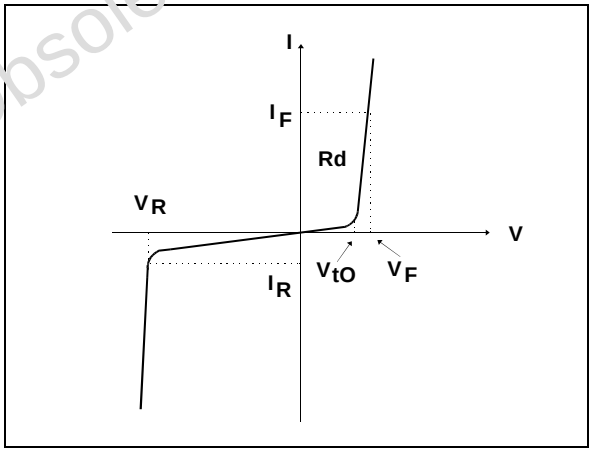


Fig. E : STATIC CHARACTERISTICS.



Conduction losses :

$P1 = V_{t0} \times I_{F(AV)} + R_d \times I_F{}^2{}_{(RMS)}$

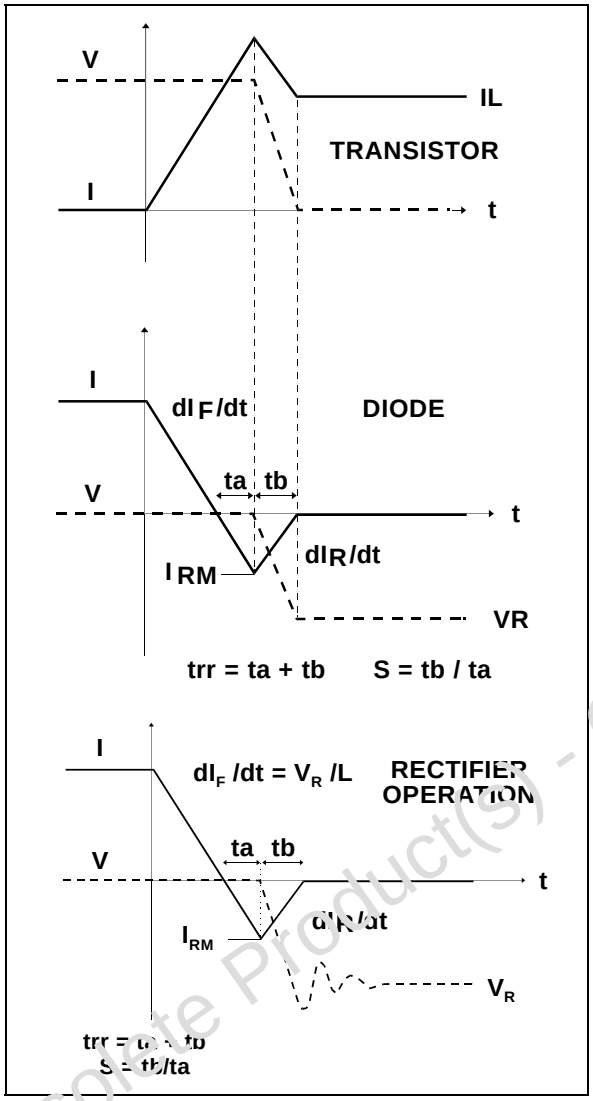
Reverse losses :

$P2 = V_R \times I_{R \times (1 - \delta)}$

Obsolete Product(s) - Obsolete Product(s)

APPLICATION DATA (Cont'd)

Fig. F : TURN-OFF CHARACTERISTICS.



Turn-on losses :
(in the transistor, due to the diode)

$$P5 = \frac{V_R \times I_{RM}^2 \times (3+2 \times S)\ F}{6\ x\ dI_F/dt} + \frac{V_R \times I_{RM} \times I_L \times (S+2) \times F}{2 \times d_{IF}/dt}$$

Turn-off losses :

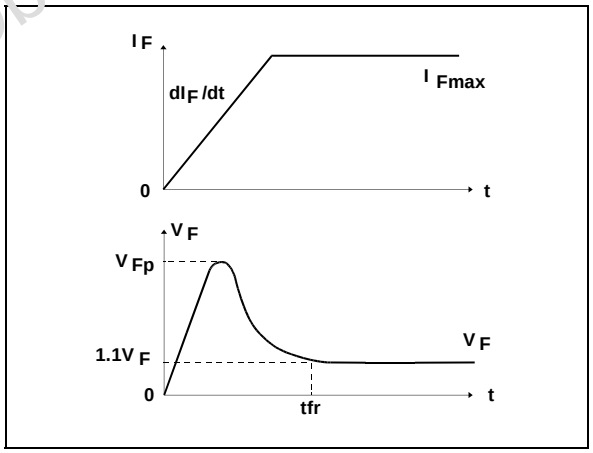
$$P3 = \frac{V_R \times I_{RM}^2 \times S \times F}{6\ x\ dI_F/dt}$$

Turn-off losses :
with non negligible serial inductance

$$P3' = \frac{V_R \times I_{RM}^2 \times S \times F}{6\ x\ dI_F/dt} + \frac{L \times I_{RM}^2 \times F}{2}$$

P3, P3' and P5 are suitable for power MOSFET and IGBT

Fig. G : TURN-ON CHARACTERISTICS.



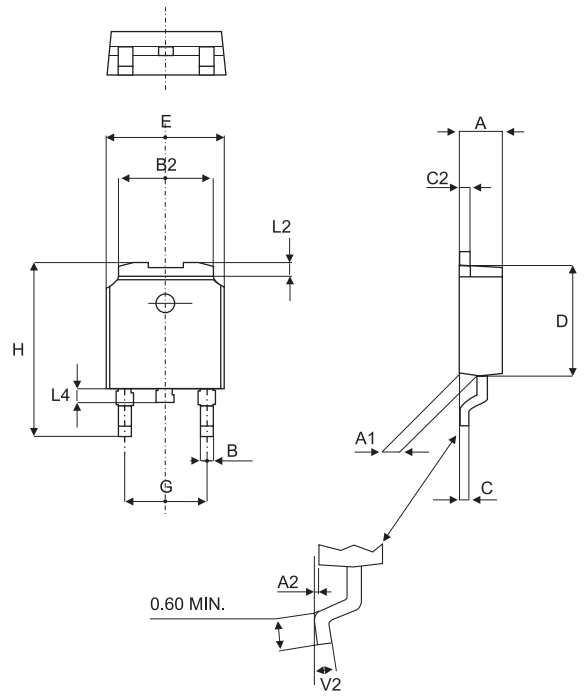
Turn-on losses :

P4 = 0.4 (V_{FP} - V_F) x I_{Fmax} x t_{fr} x F

Obsolete Product(s) - Obsolete Product(s)

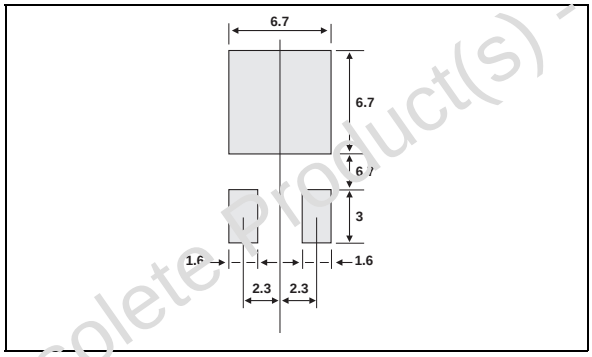
PACKAGE MECHANICAL DATA

DPAK



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max	Min.	Max.
A	2.20	2.40	0.086	0.094
A1	0.90	1.10	0.035	0.043
A2	0.03	0.23	0.001	0.009
B	0.64	0.90	0.025	0.035
B2	5.20	5.40	0.204	0.212
C	0.45	0.60	0.017	0.023
C2	0.48	0.60	0.018	0.023
D	6.00	6.20	0.236	0.244
E	6.40	6.60	0.251	0.259
G	4.40	4.60	0.173	0.181
H	9.35	10.10	0.368	0.397
L2	0.80 typ.		0.031 typ.	
L4	0.60	1.00	0.023	0.039
V2	0°	8°	0°	8°

FOOTPRINT DIMENSIONS (in millimeters)



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTA312B	A312	DPAK	0.3g	75	Tube
STTA312B-TR	A312	DPAK	0.3g	2500	Tape & reel

- Epoxy meets UL94,V0

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